

# Fabrication, characterization and testing of sílícon photomultíplíers for the Muon Portal Project



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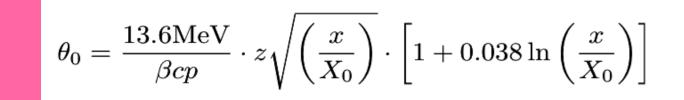
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# SiPM application: the Muon Portal Project

Apparatus designed to inspect the travelling cargo containers using the muon tomography technique.

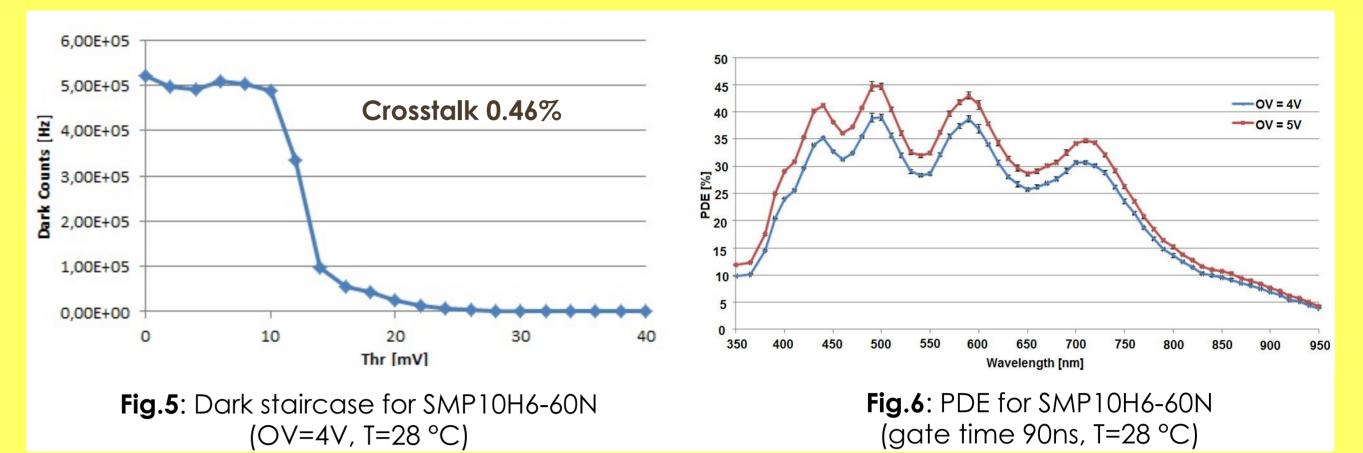


This technique is based on the determination of the scattering angle of cosmic muons induced by heavy materials.

## **Optical characterization**

## Photon Detection Efficiency and DCR measurements

Monochromatic light sent to an integrating sphere hosting a calibrated reference photodiode and the SiPM under test (MUON60-1mm<sup>2</sup> device).

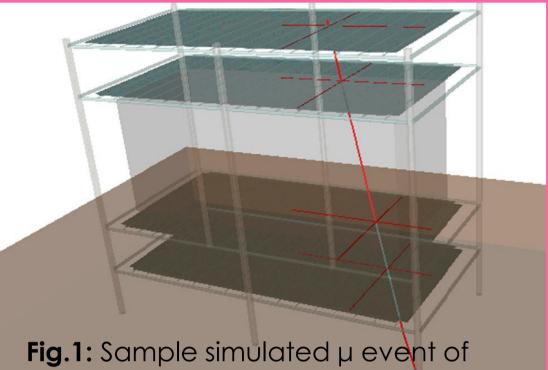


- $\beta c \rightarrow \text{Velocity}$  $p \rightarrow Momentum$
- $z \rightarrow \text{Charge Number}$

### **Specifications of the Muon Portal Detector**

 $x \rightarrow \text{Width of Medium}$ 

 $X_0 \rightarrow \text{Radiation Length}$ 



energy1GeV with hits produced in the 4 detector planes.

## ✓ 8 physical detection planes (4 XY logical planes) Each plane segmented into 6 modules (1m x 3m) ✓ Modules consist of 100 strips of extruded scintillator with double WLS fibre readout ✓ High PDE, high fill-factor SiPM as

readout sensors

## Activities and timeline

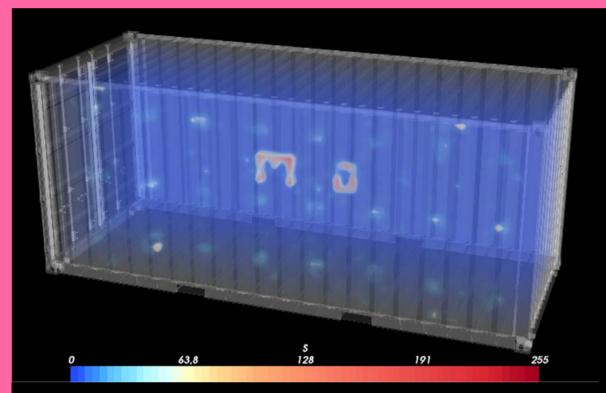


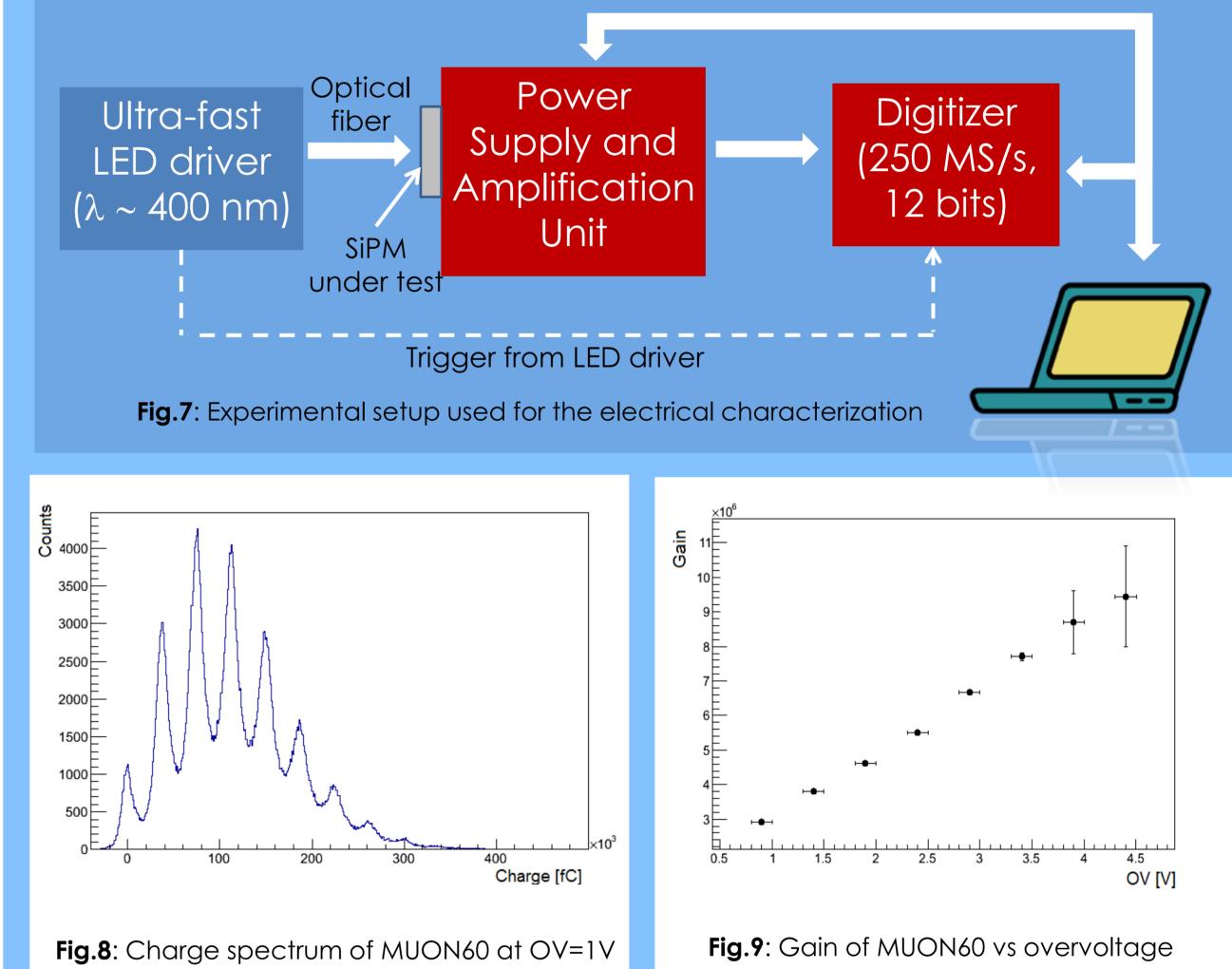
Fig.2: Tomographic imaging of a simulated

- ✓ Construction of 48 modules Characterization and tests of the SiPMs
- ✓ Test of the FE and Readout electronics
- ✓ GEANT4 replica of the full detector
- ✓ Development of imaging algorithms
- $\checkmark$  End of construction expected by

#### **Electrical characterization** 4.

## Charge spectrum and gain measurement

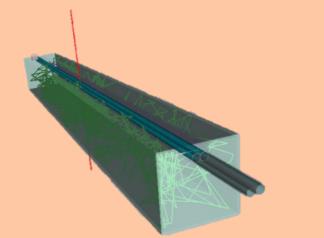
Experimental setup based on the CAEN SiPM evaluation kit.



#### scenario (MUON shape surrounded by washing mid 2015 machines, with M: U, U:Fe, O:Pb, N:Al)

#### SiPM technology 2.

Silicon PhotoMultipliers custom-made by STMicroelectronics n-on-p technology.



- Compactness  $\checkmark$
- Cost-effective  $\checkmark$
- Low voltages required  $\checkmark$
- ✓ High PDE to light from WLS fibres
- ✓ High Fill Factor
- Several prototypes built,  $\checkmark$ customized for this application

## **Final design**

4 independent round shaped SiPMs ( $\phi$ ~1.5 mm)  $\checkmark$  2 MUON60 = SiPMs with 60 µm cell pitch  $\checkmark$  2 MUON75 = SiPMs with 75 µm cell pitch

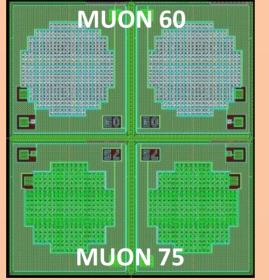
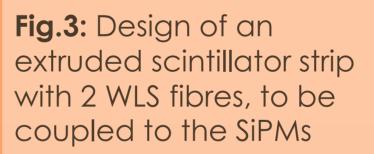


Fig.4: SiPM module layout

| Parameter  | Muon60           | Muon75           |
|--|------------------|------------------|
| Sensitive area size (mm <sup>2</sup> )                   | 19728            | 18000            |
| Number of cells  | 548              | 320              |
| Cell fill factor (%)                                     | 67.4             | 73.8             |
| Cell size (µm²)  | $60 \times 60$   | 75 × 75          |
| Quenching resistor squares number                        | 28               | 28               |
| Quenching capacitor area (µm <sup>2</sup> )              | 26               | 26               |
| Cell active area (µm <sup>2</sup> )                      | 2427             | 2427             |
| Cell perimetral area (µm <sup>2</sup> )                  | 844              | 844              |
| Diode bonding pad area (µm <sup>2</sup> )                | $140 \times 140$ | $140 \times 140$ |
| SiPM bonding pad area (µm <sup>2</sup> )                 | $140 \times 140$ | $140 \times 140$ |
| Metal grid area (pads included) ( $\mu$ m <sup>2</sup> ) | 124392           | 97828            |

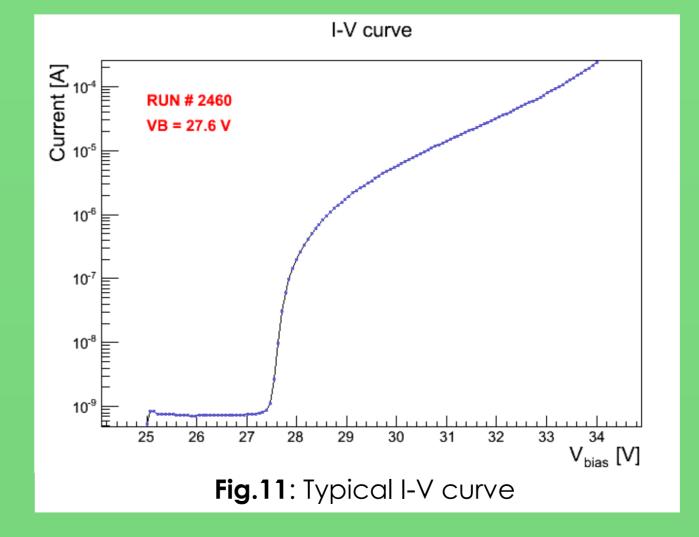


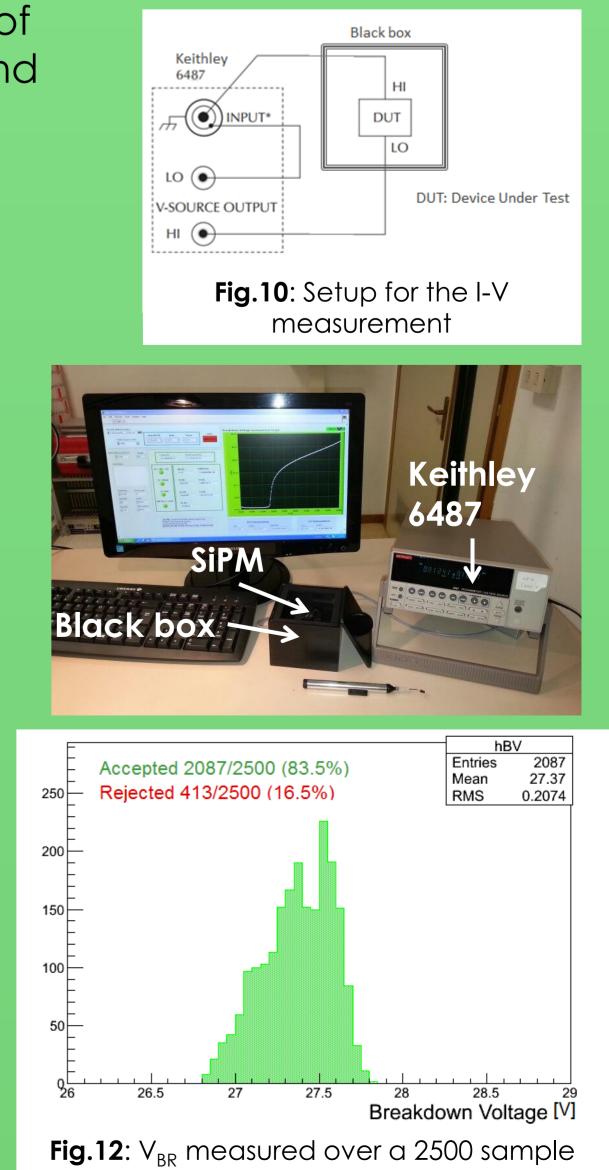
#### SiPM classification 5.

SiPMs with similar characteristics (in terms of breakdown voltage BV and current) will be installed in the same region of the

detector in order to set, for group of 10 SiPMs, the same bias voltage and threshold level.

## Selection criteria







7<sup>th</sup> International Conference on New Developments in Photodetection Tours, France, June 30th to July 4th 2014

After the construction of the I-V curve, SiPMs not satisfying stringent criteria on the BV will be rejected (i.e. BV < 27 or BV > 29). Other selection criteria are applied to the current values corresponding to BV+5V and BV-2V.